

PATENT

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**REVOCATION OF POWER OF ATTORNEY,
NEW POWER OF ATTORNEY BY ASSIGNEE AND
CHANGE OF CORRESPONDENCE ADDRESS**

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

Customer No. 20792
Myers Bigel Sibley & Sajovec, P.A.
P. O. Box 37428
Raleigh, North Carolina 27627
Telephone: (919) 854-1400
Facsimile: (919) 854-1401

Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patent application identified to Hewlett-Packard Development Company, L.P. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jeong-Taek Kong
Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: Aug. 23, 2007

APPENDIX A

| In re | Serial No. | Filed | Title | Assignment Recorded | Res. | Frame: | Att. Dkt. No. |
|---------------|------------|----------|---|---------------------|----------------------------|----------------------|---------------|
| Adelmann | 10/62,632 | 07/17/03 | Assisted Memory Device with Integrated Cache | Samsung 07/18/03 | 014138 015613 015611 | 0051 0070 0239 | 5649-2218 |
| Smith | 10/743,662 | 12/22/03 | MRAM with Controller | Samsung 07/26/07 | 014841 019611 | 0615 0239 | 5649-2219 |
| Perner | 11/252,143 | 10/17/05 | System and Method for Reading a Memory Cell | HPDC 12/22/03 | 019611 | 0239 | |
| Anthony | 11/021,268 | 12/23/04 | Magnetic Memory Device and Methods for Making Same | HPDC 07/26/07 | 014930 019612 | 0571 0436 | 5649-2220 |
| Jedwab | 10/722,918 | 11/26/03 | Magnetic Memory which Compares Compressed Fault Maps | HPDC 02/10/03 | 013737 013776 | 0985 0928 | 5649-2221 |
| Selek | 10/700,203 | 11/03/03 | Magnetic Memory | HPDC 06/18/03 | 019611 | 0807 | |
| Pline | 10/725,855 | 12/02/03 | Data Storage System with Error Correction Code and Replaceable Defective Memory | Samsung 07/26/07 | 014756 019611 | 0631 0690 | 5649-2222 |
| Spencer | 11/203,755 | 8/15/05 | Method of Packaging Magnetic Memory | HPDC 11/26/03 | 013801 019611 | 0643 0632 | 5649-2225 |
| Lee | 10/698,501 | 10/31/03 | Heating MRAM Cells to Ease State Switching | HPDC 06/22/04 | 014764 019611 | 0438 0135 | 5649-2223 |
| Stobbs | 10/631,404 | 07/30/03 | Magnetic Shielding for Magnetic Random Access Memory | HPDC 12/2/03 | 014757 019611 | 0280 0155 | 5649-2224 |
| Tausig | 10/914,255 | 08/09/04 | Silver Island Anti-Fuse | Samsung 07/26/07 | 013801 019611 | 0643 0853 | 5649-2226 |
| Sharma | 10/144,927 | 04/16/03 | Optical Signal Transmission Transducer | HPDC 06/29/03 | 013719 019612 | 0107 0754 | 5649-2226 |
| Perner | 11/264,539 | 11/01/05 | Controllably Connectable Strings of MRAM Cells | HPDC 09/11/03 | 013991 019611 | 0927 0936 | 5649-2227 |
| Nickel | 10/315,748 | 12/10/02 | Thermally-Assisted Switching of Magnetic Memory Elements | HPDC 07/26/07 | 015678 019612 | 0022 0029 | 5649-2228 |
| Lee | 10/692,612 | 10/24/03 | A Method of Making a Magnetic Tunnel Junction Device | HPDC 11/01/05 | 017180 019612 | 0026 0029 | 5649-2231 |
| Nauka | 10/698,717 | 10/31/03 | Data Storage Device Including Conductive Probe and Ferroelectric Storage Medium | Samsung 07/26/07 | 011938 019612 | 0238 0928 | 5649-2232 |
| Perner et al. | 10/698,896 | 10/31/03 | Multi-Sample Read Circuit Having Test Mode of Operation | HPDC 06/22/01 | 011938 019614 | 0059 0059 | 5649-2233 |
| Nickel | 10/733,089 | 12/11/03 | Using Sense Lines to Thermally Control the State of an MRAM | Samsung 07/26/07 | 014461 019612 | 0725 0139 | 5649-2235 |
| | | | | Samsung 07/26/07 | 014817 019613 | 0794 0913 | 5649-2236 |

APPENDIX A

| In re: | Serial No.: | Filed: | Title: | Assignment Recorded: | Res.: | Frame: | Aut. Dist. No.: |
|---------------|-------------|----------|--|------------------------------------|----------|--------|-----------------|
| Nickel | 10/934,922 | 09/02/04 | Thin Film Device and a Method of Formation Thereof | HPPDC 09/02/04 Samsung 07/26/07 | 01961.12 | 0240 | 5649-2237 |
| Perner | 10/934,243 | 09/03/04 | Method and Apparatus for Multi-Plane MRAM | HPPDC 09/03/04 Samsung 07/26/07 | 01961.13 | 0064 | 5649-2238 |
| Zhang | 10/721,574 | 11/25/03 | Molecular Optoelectronic Memory Device | HPPDC 03/31/04 Samsung 07/26/07 | 01447.8 | 0520 | 5649-2239 |
| Sharma | 11/285,991 | 11/23/05 | Multi-Layered Magnetic Memory Structures | HPPDC 11/23/05 Samsung 07/26/07 | 01728.1 | 0685 | 5649-2240 |
| Sharma | 11/118,828 | 04/29/05 | Process for Forming Magnetic Memory Structures | HPPDC 04/29/05 Samsung 07/26/07 | 01961.13 | 0412 | 5649-2241 |
| Sharma | 11/286,245 | 11/23/05 | Multi-Layered Magnetic Memory Structures | HPPDC 11/23/05 Samsung 07/26/07 | 01728.1 | 0810 | 5649-2242 |
| Sharma et al. | 11/286,009 | 11/23/05 | Multi-Layered Magnetic Memory Structures | HPPDC 11/23/05 Samsung 07/26/07 | 01961.13 | 0465 | 5649-2243 |
| Perner | 11/286,861 | 11/03/05 | Analog Preamplifier Calibration | HPPDC 11/03/05 Samsung 07/26/07 | 01719.5 | 0971 | 5649-2244 |
| Perner | 11/287,705 | 11/03/05 | Digital Current Source | HPPDC 11/03/05 Samsung 07/26/07 | 01961.11 | 0576 | 5649-2245 |
| Nickel | 11/050,273 | 02/03/05 | Method of Fabricating a Manganese Diffusion Barrier | HPPDC 06/06/06 Samsung 07/26/07 | 01630.6 | 0539 | 5649-2247 |
| Eaton | 10/661,448 | 09/11/03 | Increased Magnetic Memory Array Sizes and Operating Margins | HPPDC 12/03/03 Samsung 07/26/07 | 01417.1 | 0302 | 5649-2248 |
| Sharma | 10/831,110 | 04/26/04 | Data Input Device That Utilizes A Layer Of Magnetic Particles To Store Non-Volatile Input Data That Is Magnetically Coupled To An Underlying MRAM Array (As Amended) | HPPDC 04/26/04 Samsung 07/26/07 | 01522.6 | 0350 | 5649-2249 |
| Nickel | 11/034,418 | 01/12/05 | RF Field Heated Diodes for Providing Thermally Assisted Switching of Magnetic Memory Elements | HPPDC 01/12/05 Samsung 07/26/07 | 01618.0 | 0951 | 5649-2250 |